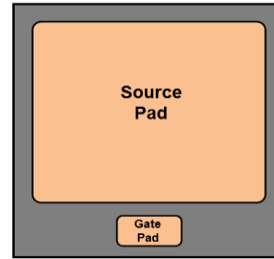


Description

United Silicon Carbide, Inc offers the high-performance G3 SiC normally-on JFET transistors. This series exhibits ultra-low on resistance ($R_{DS(ON)}$) and gate charge (Q_G) allowing for low conduction and switching loss. The device normally-on characteristics with low $R_{DS(ON)}$ at $V_{GS} = 0\text{ V}$ is also ideal for current protection circuits without the need for active control, as well as for cascode operation.



Part Number	Package
UJ3N120035	Undiced wafer
UJ3N120035Z	Die on tape

Features

- ◆ Typical on-resistance $R_{DS(on),typ}$ of 35mΩ
- ◆ Voltage controlled
- ◆ Maximum operating temperature of 175°C
- ◆ Extremely fast switching not dependent on temperature
- ◆ Low gate charge
- ◆ Low intrinsic capacitance
- ◆ RoHS compliant

Typical Applications

- ◆ Over current protection circuits
- ◆ DC-AC inverters
- ◆ Switch mode power supplies
- ◆ Power factor correction modules
- ◆ Motor drives
- ◆ Induction heating

Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
Drain-source voltage	V_{DS}		1200	V
Gate-source voltage	V_{GS}	DC	-20 to +3	V
		AC ⁽¹⁾	-20 to +20	
Continuous drain current ^(2,3)	I_D	$T_C = 25^\circ\text{C}$	63	A
		$T_C = 100^\circ\text{C}$	46	A
Pulsed drain current ^(3,4)	I_{DM}	$T_C = 25^\circ\text{C}$	185	A
Maximum junction temperature ⁽⁵⁾	$T_{J,max}$		175	°C
Operating and storage temperature	T_J, T_{STG}		-55 to 175	°C

(1) +20V AC rating applies for turn-on pulses <200ns applied with external $R_G > 1\Omega$.

(2) Limited by $T_{J,max}$

(3) Assumes a maximum junction-to-case thermal resistance of 0.35°C/W

(4) Pulse width t_p limited by $T_{J,max}$

(5) Package limited

Electrical Characteristics ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Typical Performance - Static

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Drain-source breakdown voltage	BV_{DS}	$V_{GS} = -20\text{V}, I_D = 1\text{mA}$	1200			V
Total drain leakage current	I_D	$V_{DS} = 1200\text{V}, V_{GS} = -20\text{V}, T_J = 25^\circ\text{C}$		10	60	μA
		$V_{DS} = 1200\text{V}, V_{GS} = -20\text{V}, T_J = 175^\circ\text{C}$		35		
Total gate leakage current	I_G	$V_{GS} = -20\text{V}, T_J = 25^\circ\text{C}$		12	100	μA
		$V_{GS} = -20\text{V}, T_J = 175^\circ\text{C}$		50		
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 2\text{V}, I_D = 20\text{A}, T_J = 25^\circ\text{C}$		31		$\text{m}\Omega$
		$V_{GS} = 0\text{V}, I_D = 20\text{A}, T_J = 25^\circ\text{C}$		35	45	
		$V_{GS} = 2\text{V}, I_D = 20\text{A}, T_J = 175^\circ\text{C}$		68		
		$V_{GS} = 0\text{V}, I_D = 20\text{A}, T_J = 175^\circ\text{C}$		76		
Gate threshold voltage	$V_{G(th)}$	$V_{DS} = 5\text{V}, I_D = 70\text{mA}$	-14	-11.5	-6	V
Gate resistance	R_G	$f = 1\text{MHz}, \text{open drain}$		2.4		Ω

Typical Performance - Dynamic (Refer to the datasheet of the packaged device UJ3N120035K3S)

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Input capacitance	C_{iss}	$V_{DS} = 100V,$ $V_{GS} = -20V,$ $f = 100kHz$		2145		pF
Output capacitance	C_{oss}			180		
Reverse transfer capacitance	C_{rss}			172		
Effective output capacitance, energy related	$C_{oss(er)}$	$V_{DS} = 0V$ to 800V, $V_{GS} = -20V$		105		pF
Total gate charge	Q_G	$V_{DS}=800V, I_D = 40A,$ $V_{GS}=-18V$ to 0V		235		nC
Gate-drain charge	Q_{GD}			130		
Gate-source charge	Q_{GS}			25		
Turn-on delay time	$t_{d(on)}$	$V_{DS}=800V, I_D=40A,$ Gate Driver = -18V to 0V, $R_{G,EXT} = 1\Omega,$ Inductive Load, FWD: UJ3D1220KSD $T_J = 25^\circ C$		25		ns
Rise time	t_r			37		
Turn-off delay time	$t_{d(off)}$			48		
Fall time	t_f			39		
Turn-on energy	E_{ON}			935		
Turn-off energy	E_{OFF}		828			
Total switching energy	E_{TOTAL}		1763			
Turn-on delay time	$t_{d(on)}$	$V_{DS}=800V, I_D=40A,$ Gate Driver = -18V to 0V, $R_{G,EXT} = 1\Omega,$ Inductive Load, FWD: UJ3D1220KSD $T_J = 150^\circ C$		24		ns
Rise time	t_r			35		
Turn-off delay time	$t_{d(off)}$			43		
Fall time	t_f			37		
Turn-on energy	E_{ON}			880		
Turn-off energy	E_{OFF}		800			
Total switching energy	E_{TOTAL}		1680			

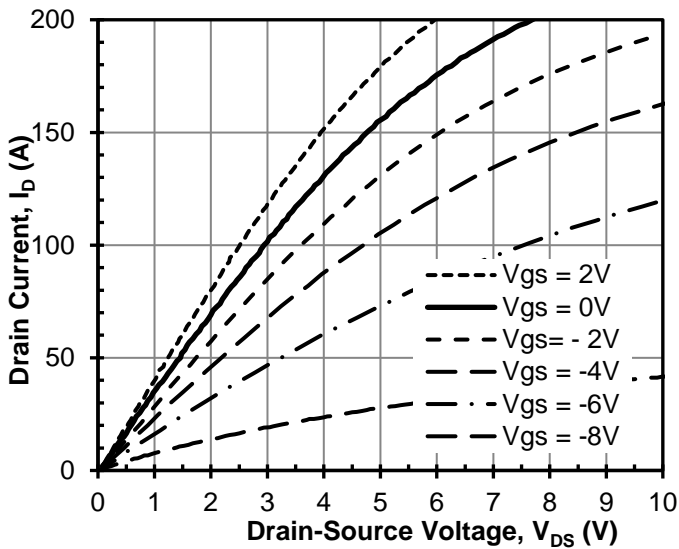
Typical Performance Diagrams


Figure 1 Typical output characteristics
at $T_J = -55^\circ\text{C}$

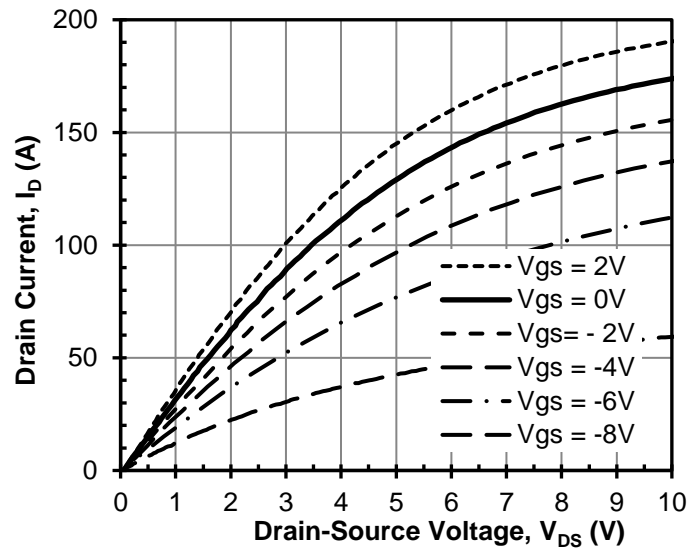


Figure 2 Typical output characteristics
at $T_J = 25^\circ\text{C}$

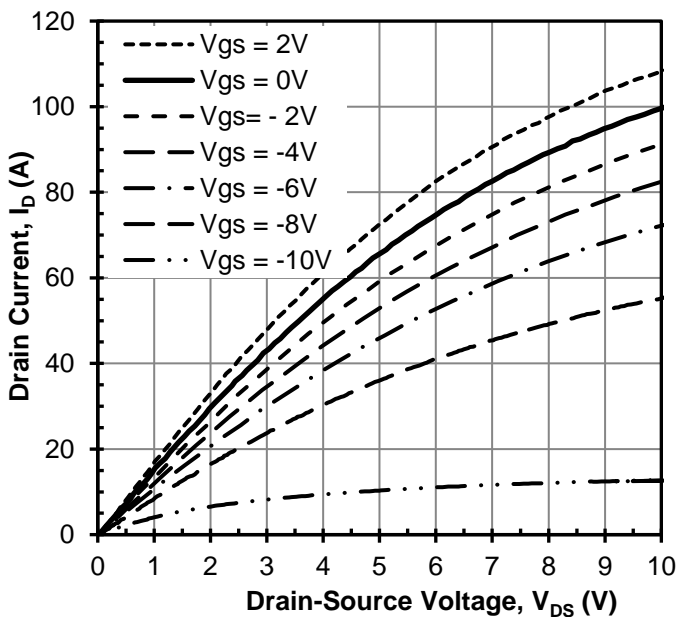


Figure 3 Typical output characteristics
at $T_J = 175^\circ\text{C}$

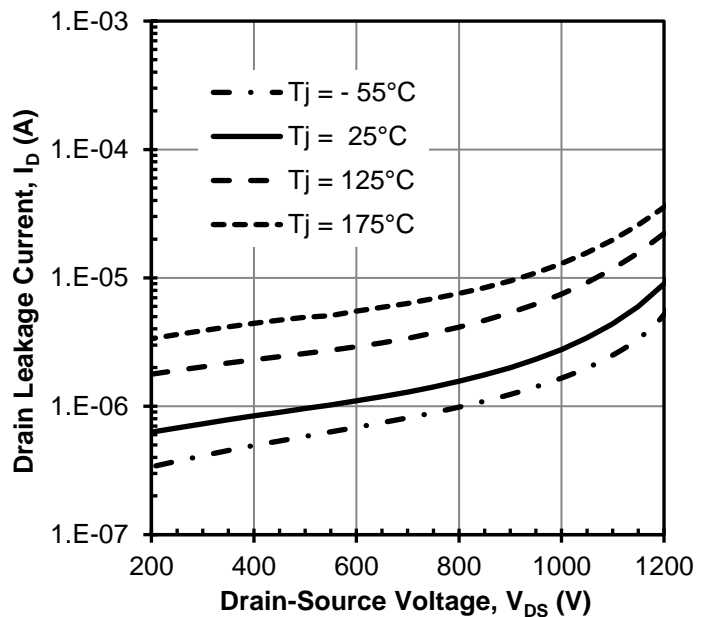


Figure 4 Typical drain-source leakage
at $V_{GS} = -20\text{V}$

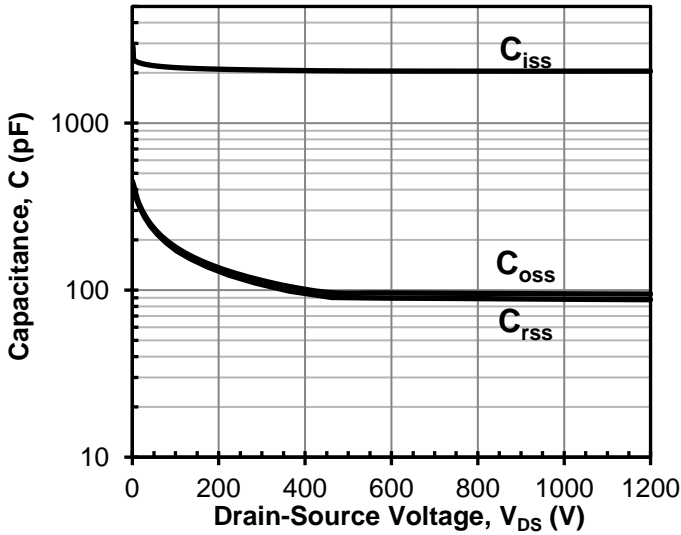


Figure 5 Typical capacitances at 100kHz and $V_{GS} = -20V$

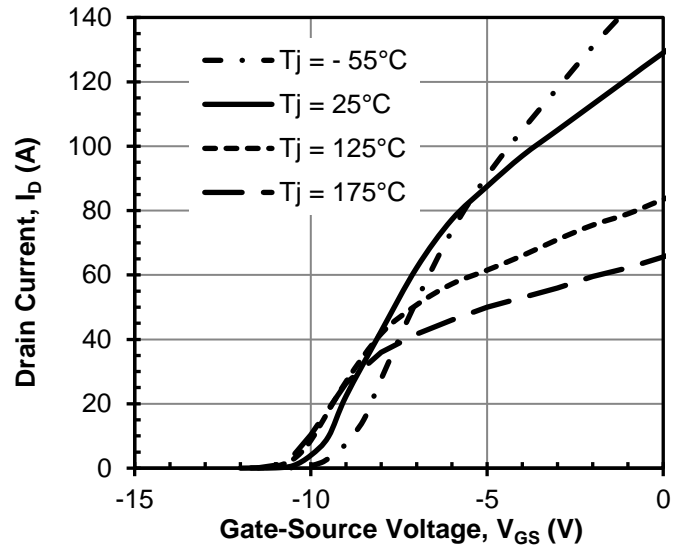


Figure 6 Typical transfer characteristics at $V_{DS} = 5V$

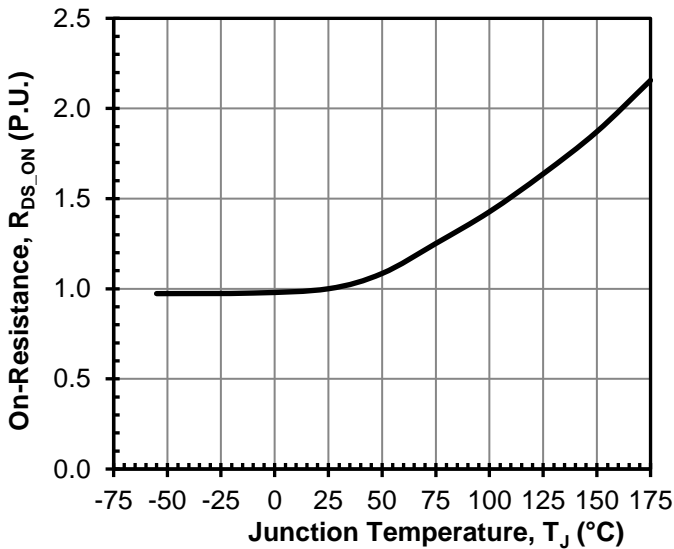


Figure 7 Normalized on-resistance vs. temperature at $V_{GS} = 0V$ and $I_D = 20A$

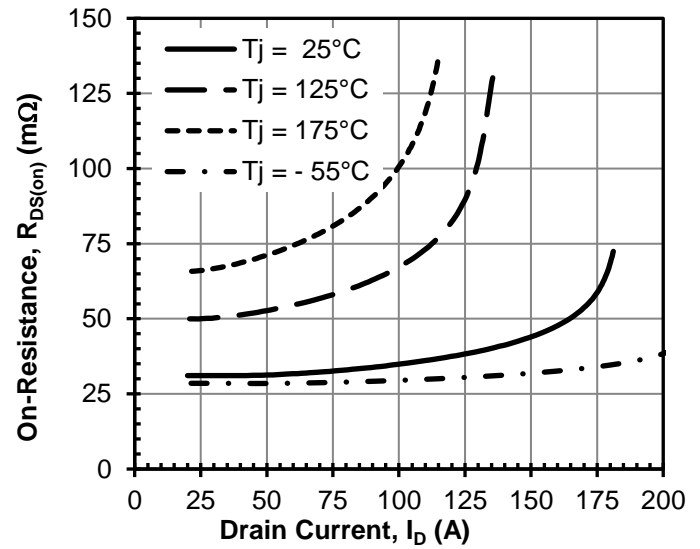


Figure 8 Typical drain-source on-resistance at $V_{GS} = 0V$

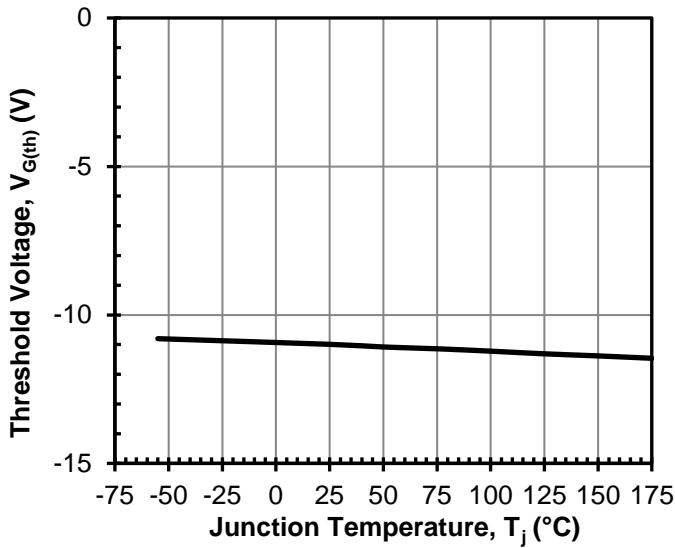


Figure 9 Threshold voltage vs. T_j
at $V_{DS} = 5V$ and $I_D = 70mA$

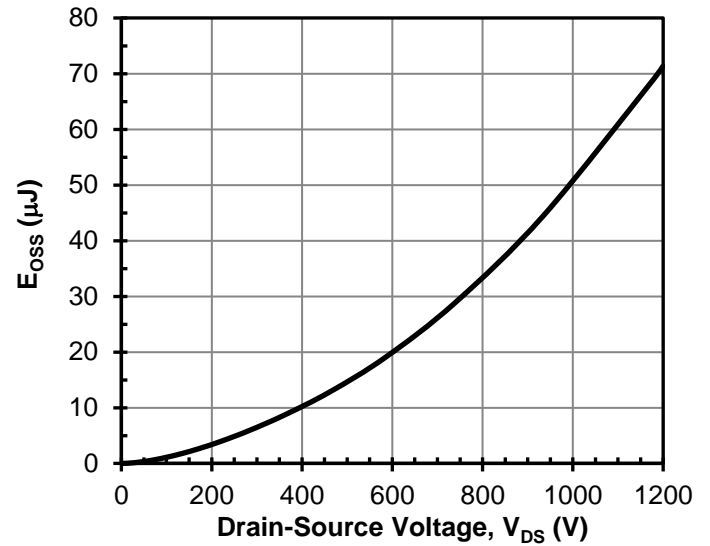


Figure 10 Typical stored energy in C_{OSS}
at $V_{GS} = -20V$

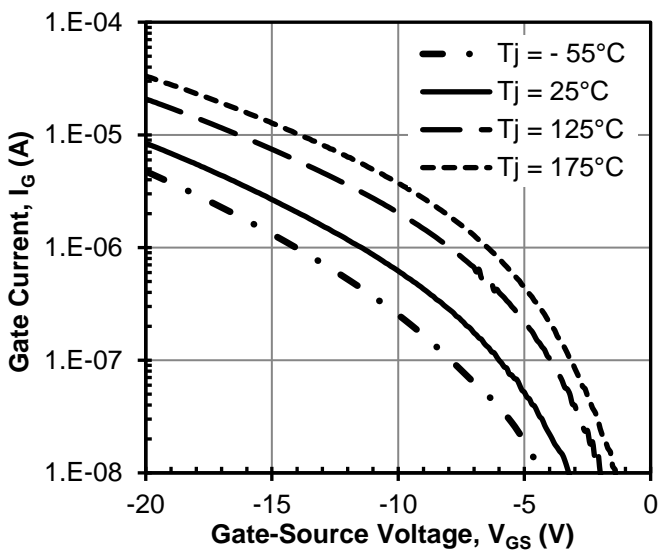


Figure 11 Typical gate leakage current
at $V_{DS} = 0V$

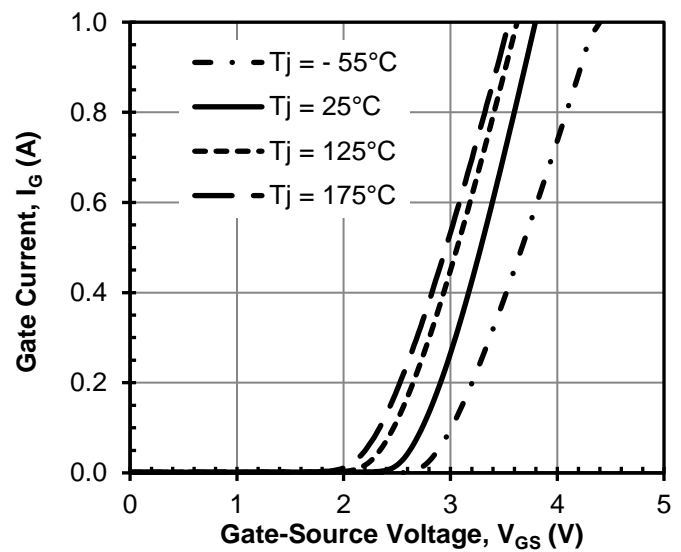


Figure 12 Typical gate forward current
at $V_{DS} = 0V$

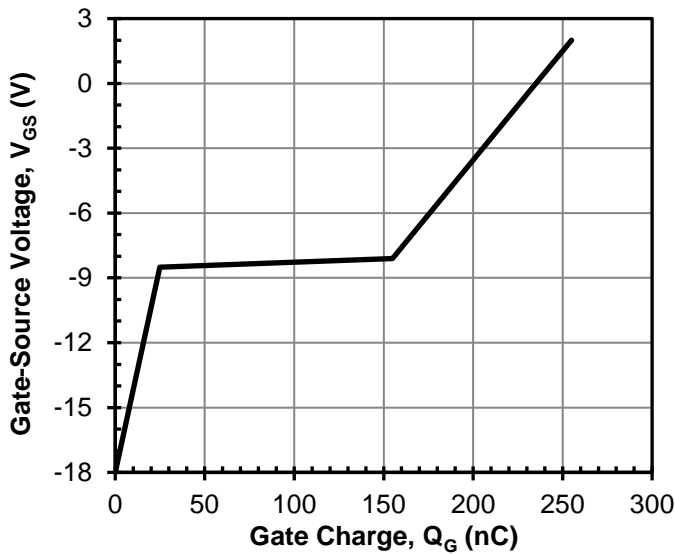


Figure 13 Typical gate charge
at $V_{DS} = 800V$ and $I_D = 40A$

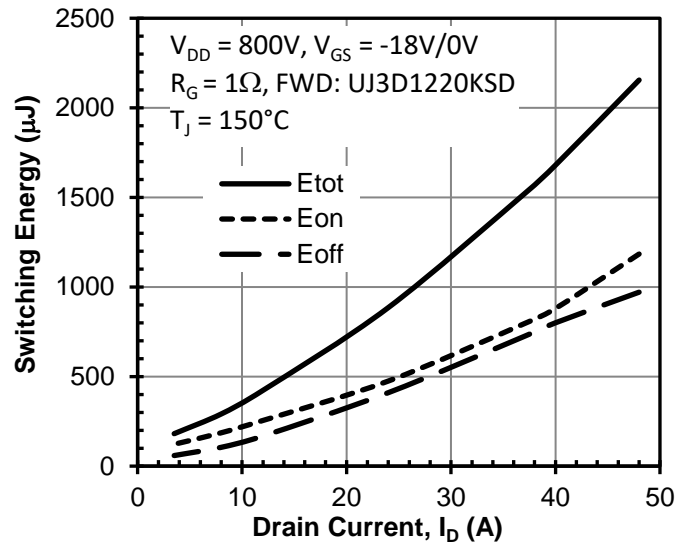


Figure 14 Clamped inductive switching energy
vs. drain current at $T_J = 150^\circ C$

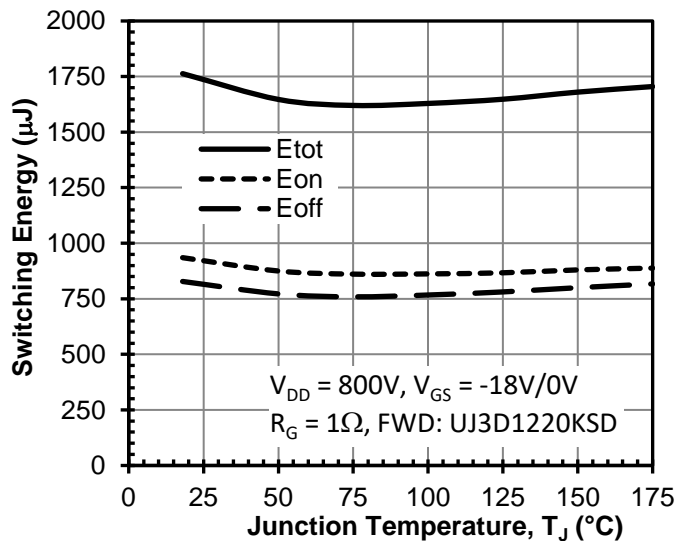


Figure 15 Clamped inductive switching energy
vs. junction temperature at $I_D = 40A$

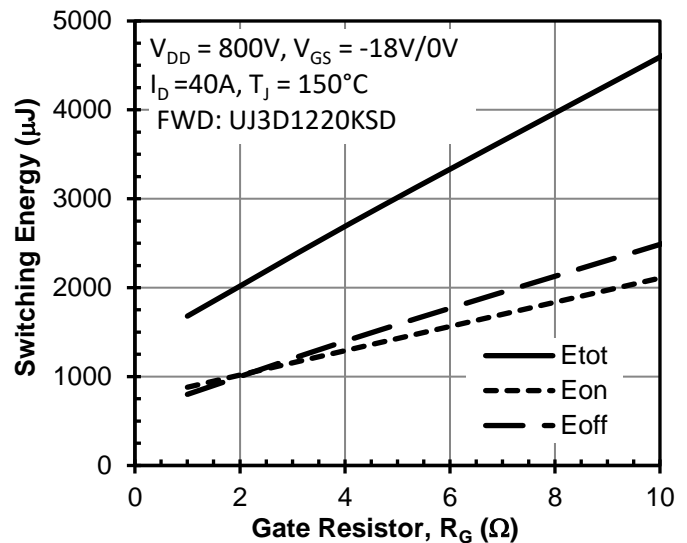
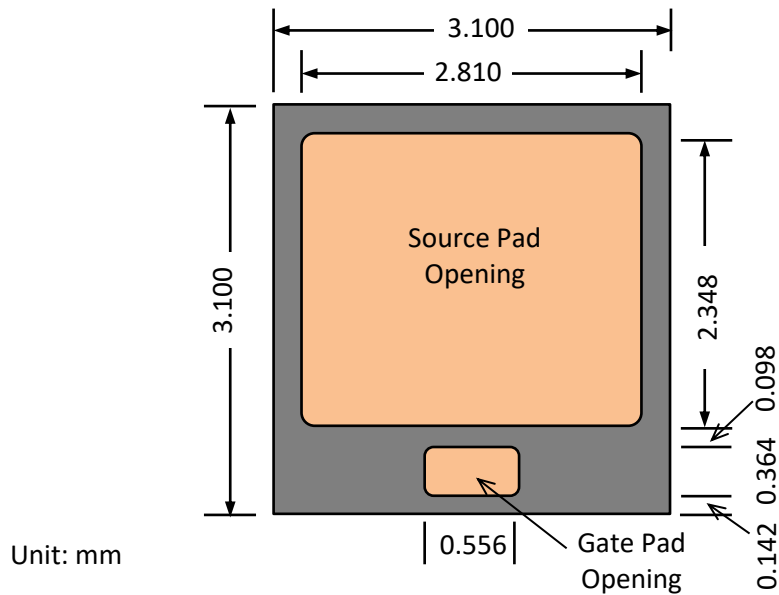


Figure 16 Clamped inductive switching energy
vs. gate resistor R_G

Mechanical Characteristics

Parameter	Typical Value	Units
Die Dimensions with Scribe Line (L x W)	3.100 x 3.100	mm
Scribe Line width	80	μm
Source Pad Metal Dimensions (L x W)	2.812 x 2.348	mm
Gate Pad Metal Dimensions (L x W)	0.556 x 0.364	mm
Source Metallization (AlCu)	5	μm
Gate Metallization (AlCu)	5	μm
Backside Drain Metallization (Ti/Ni/Ag)	0.1/0.2/1	μm
Frontside Passivation	Polyimide	
Die Thickness	150	μm
Wafer Size	150	mm
Gross Die Per Wafer	1,451	

Chip Dimensions

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